

NCE N-Channel Enhancement Mode Power MOSFET

Description

The NCE6003XM uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge. This device is suitable for use as a Battery protection or in other switching application.

General Features

V_{DS} =60V,I_D =3A

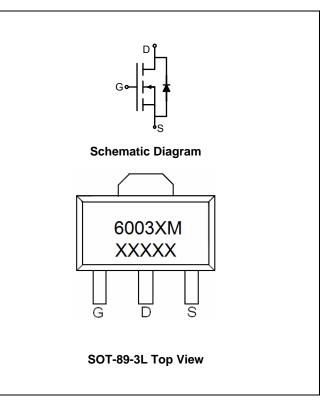
 $R_{DS(ON)}$ <90m Ω @ V_{GS} =10V

 $R_{DS(ON)}$ < 110m Ω @ V_{GS} =4.5V

- High power and current handing capability
- Lead free product is acquired
- Surface mount package

Application

- Battery switch
- ●DC/DC converter



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
6003XM	NCE6003XM	SOT-89-3L	Ø180mm	12mm	1000 units

Absolute Maximum Ratings (T_A=25 ℃ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	60	V
Gate-Source Voltage	V _G s	±20	V
Drain Current-Continuous	I _D	3	А
Drain Current-Pulsed (Note 1)	I _{DM}	10	Α
Maximum Power Dissipation	P _D	1.7	W
Operating Junction and Storage Temperature Range	T_{J}, T_{STG}	-55 To 150	°C

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	73.5	°C/W

Electrical Characteristics (T_A=25 ℃ unless otherwise noted)

Parameter	Symbol	ol Condition		Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	60	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =60V,V _{GS} =0V	-	-	1	μA



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NCE6003XM

Gate-Body Leakage Current	I_{GSS}	V_{GS} =±20 V , V_{DS} =0 V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =250μA	0.9	1.3	2.0	V
Drain-Source On-State Resistance	В	V _{GS} =10V, I _D =3A	-	68	90	mΩ
Diani-Source On-State Resistance	$R_{DS(ON)}$	V _{GS} =4.5V, I _D =3A	-	80	110	mΩ
Forward Transconductance	g FS	V_{DS} =5 V , I_{D} =3 A	-	3	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{lss}	\/ -20\/\/ -0\/	-	270	-	PF
Output Capacitance	Coss	V_{DS} =30V, V_{GS} =0V, F=1.0MHz	-	30	-	PF
Reverse Transfer Capacitance	C _{rss}	r-1.0ivinz	-	21	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}		-	5	-	nS
Turn-on Rise Time	t _r	V_{DD} =30 V , I_{D} =3 A	-	10	-	nS
Turn-Off Delay Time	Delay Time $t_{d(off)}$ V_{GS} =10V, R_{GEN} =		-	12	-	nS
Turn-Off Fall Time	t _f		-	8	-	nS
Total Gate Charge	Qg	\/ -20\/ -24	-	11.5	-	nC
Gate-Source Charge	Q_{gs}	V _{DS} =30V,I _D =3A,	-	1.8	-	nC
Gate-Drain Charge	Q_{gd}	V _{GS} =10V	-	2.2	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V_{GS} =0 V , I_{S} =3 A	-	-	1.2	V
Diode Forward Current (Note 2)	Is		-	-	3	Α

Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- **2.** Surface Mounted on FR4 Board, $t \le 10$ sec.
- 3. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production



Typical Electrical and Thermal Characteristics

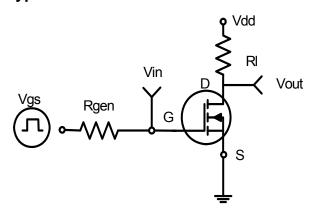
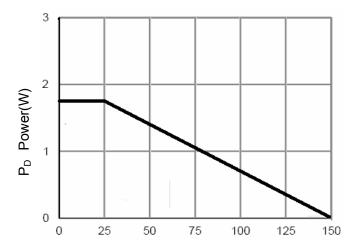


Figure 1:Switching Test Circuit



 T_J -Junction Temperature(°C) Figure 3 Power Dissipation

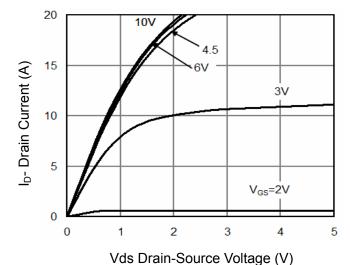


Figure 5 Output Characteristics

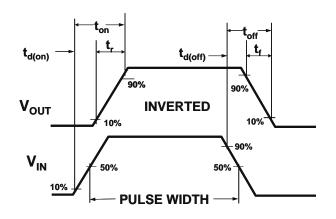
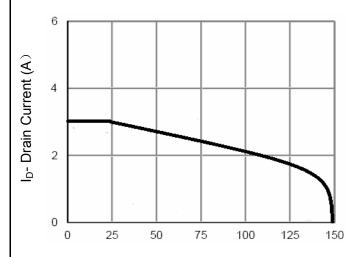


Figure 2:Switching Waveforms



T_J-Junction Temperature(°C)

Figure 4 Drain Current

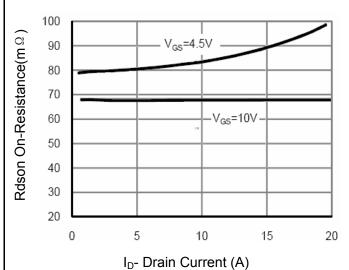


Figure 6 Drain-Source On-Resistance



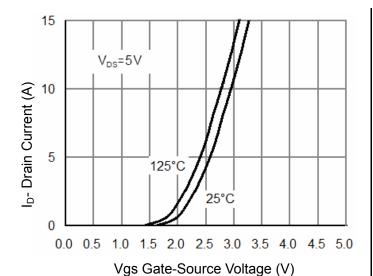
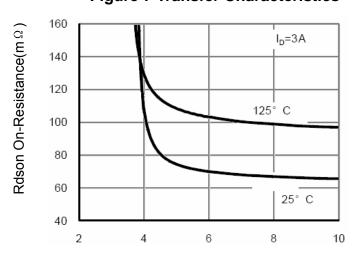


Figure 7 Transfer Characteristics



Vgs Gate-Source Voltage (V)
Figure 9 Rdson vs Vgs

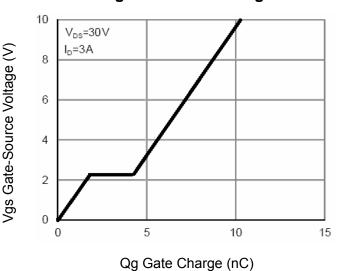


Figure 11 Gate Charge

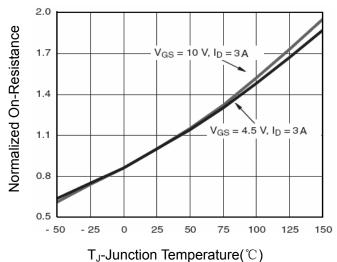


Figure 8 Drain-Source On-Resistance

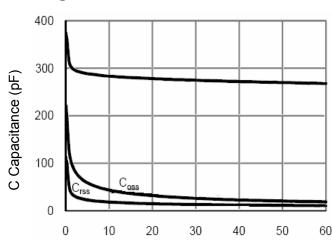


Figure 10 Capacitance vs Vds

Vds Drain-Source Voltage (V)

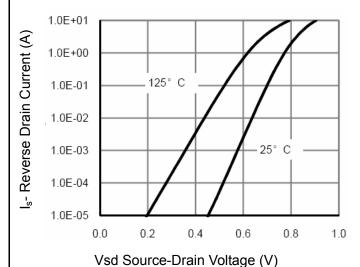
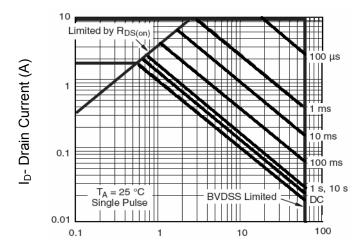


Figure 12 Source- Drain Diode Forward





Vds Drain-Source Voltage (V)

Figure 13 Safe Operation Area

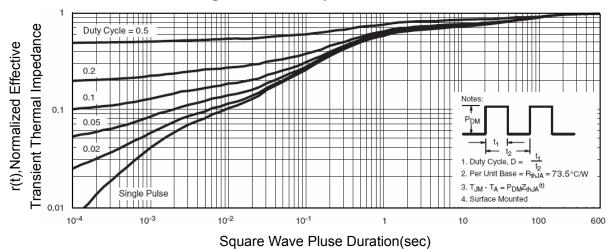
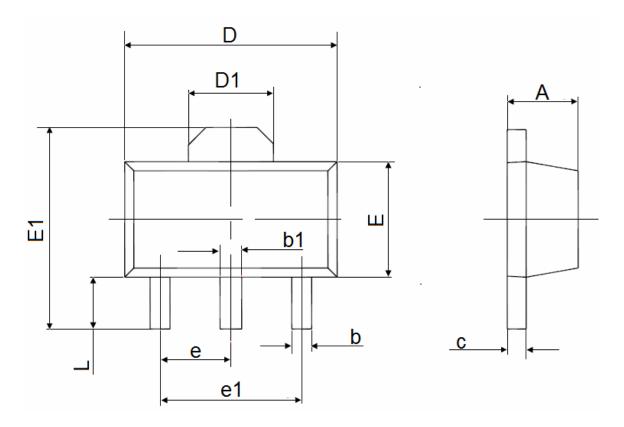


Figure 14 Normalized Maximum Transient Thermal Impedance



SOT-89-3L Package Information



Cymbol	Dimensions	In Millimeters	Dimensions In Inches		
Symbol	Min	Max	Min	Max	
Α	1.400	1.600	0.055	0.063	
b	0.320	0.520	0.013	0.020	
b1	0.400	0.580	0.016	0.023	
С	0.350	0.440	0.014	0.017	
D	4.400	4.600	0.173	0.181	
D1	1.550	1.550 REF.		REF.	
Е	2.300	2.600	0.091	0.102	
E1	3.940	4.250	0.155	0.167	
е	1.500 TYP.		0.060 TYP.		
e1	3.000 TYP.		0.118 TYP.		
L	0.900	1.200	0.035	0.047	

Notes

- 1. All dimensions are in millimeters.
- 2. Tolerance ±0.10mm (4 mil) unless otherwise specified
- 3. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.
- 4. Dimension L is measured in gauge plane.
- $5. \ Controlling \ dimension \ is \ millimeter, \ converted \ inch \ dimensions \ are \ not \ necessarily \ exact.$



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